



TRANSISTORS, HIGH VOLTAGE, NPN

BASED ON TYPE 2N5551

ESCC Detail Specification No. 5201/019

Issue 6	February 2013
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DOCUMENTATION CHANGE NOTICE

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DCR No.	CHANGE DESCRIPTION
757	Specification upissued to incorporate technical changes per DCR. Specification converted into MSWord. Changes in presentation are possible.

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1 GENERAL

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

1.2 APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:

- (a) ESCC Generic Specification No. 5000
- (b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices

1.3 TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. 21300 shall apply.

1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

1.4.1 The ESCC Component Number

The ESCC Component Number shall be constituted as follows:

Example: 520101901R

- Detail Specification Reference: 5201019
- Component Type Variant Number: 01 (as required)
- Total Dose Radiation Level Letter: R (as required)

1.4.2 Component Type Variants

The component type variants applicable to this specification are as follows:

Variant Number	Based on Type	Case	Lead/Terminal Material and/or Finish	Weight max g	Total Dose Radiation Level Letter
01	2N5551	TO-18	D2	0.4	R [100kRAD(Si)]
02	2N5551	TO-18	D3 or D4	0.4	R [100kRAD(Si)]
04	2N5551	CCP (3 Terminal)	2	0.06	R [100kRAD(Si)]
05	2N5551	CCP (3 Terminal)	4	0.06	R [100kRAD(Si)]
06	2N5551	TO-39	D2	1.5	R [100kRAD(Si)]
07	2N5551	TO-39	D3 or D4	1.5	R [100kRAD(Si)]
08	2N5551	CCP (4 Terminal)	2	0.06	R [100kRAD(Si)]
09	2N5551	CCP (4 Terminal)	4	0.06	R [100kRAD(Si)]

The lead/terminal material and/or finish shall be in accordance with the requirements of ESCC Basic Specification No. 23500.

Total dose radiation level letters are defined in ESCC Basic Specification No. 22900. If an alternative radiation test level is specified in the Purchase Order, the letter shall be changed accordingly.

1.5 MAXIMUM RATINGS

The maximum ratings shall not be exceeded at any time during use or storage.

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

Characteristics	Symbols	Maximum Ratings	Unit	Remarks
Collector-Base Voltage	V_{CBO}	180	V	Over entire operating temperature range
Collector-Emitter Voltage	V_{CEO}	160	V	
Emitter-Base Voltage	V_{EBO}	6	V	
Collector Current For TO-18 and TO-39 For CCP	I_C	600 500	mA	Continuous

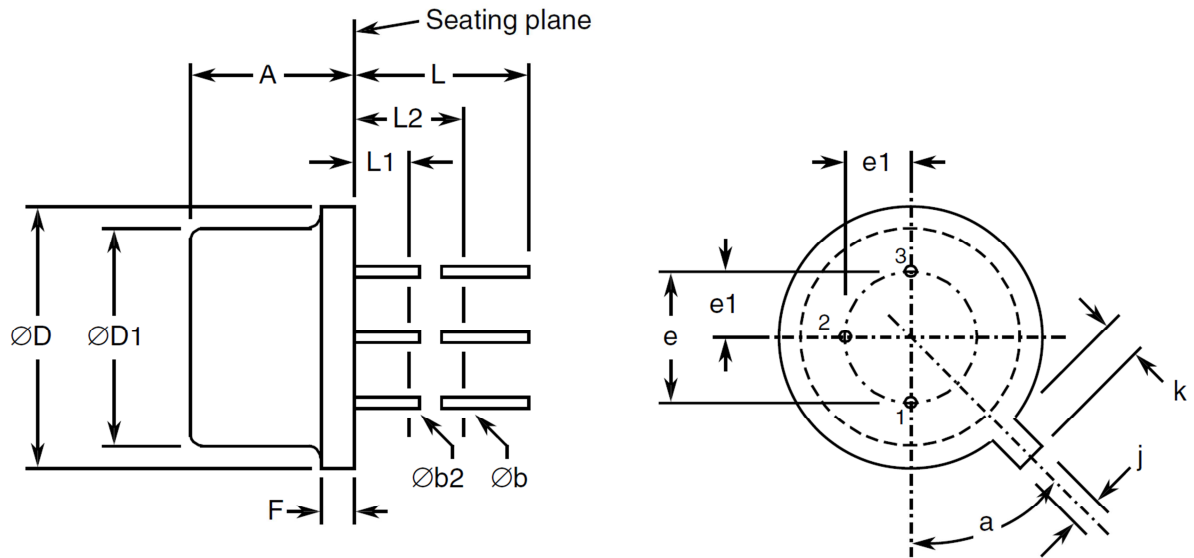
Characteristics	Symbols	Maximum Ratings	Unit	Remarks
Power Dissipation For TO-18, TO-39 and CCP For TO-18 and TO-39	P_{tot1}	0.36	W	At $T_{amb} \leq +25^{\circ}\text{C}$
	P_{tot2}	1.2	W	At $T_{case} \leq +25^{\circ}\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{th(j-a)}$	486	$^{\circ}\text{C/W}$	
Thermal Resistance, Junction-to-Case	$R_{th(j-c)}$	145.8	$^{\circ}\text{C/W}$	Note 1
Operating Temperature Range	T_{op}	-65 to +200	$^{\circ}\text{C}$	Note 2
Storage Temperature Range	T_{stg}	-65 to +200	$^{\circ}\text{C}$	Note 2
Soldering Temperature For TO-18 and TO-39 For CCP	T_{sol}	+260 +245	$^{\circ}\text{C}$	Note 3 Note 4

NOTES:

1. Thermal Resistance, Junction-to-Case applies to all TO-18 and TO-39 packaged Variants.
2. For Variants with tin-lead plating or hot solder dip lead finish all testing, and any handling, performed at $T_{amb} > +125^{\circ}\text{C}$ shall be carried out in a 100% inert atmosphere.
3. Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.
4. Duration 5 seconds maximum and the same terminal shall not be resoldered until 3 minutes have elapsed.

1.6 PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION

1.6.1 Metal Can Package (TO-18) - 3 lead

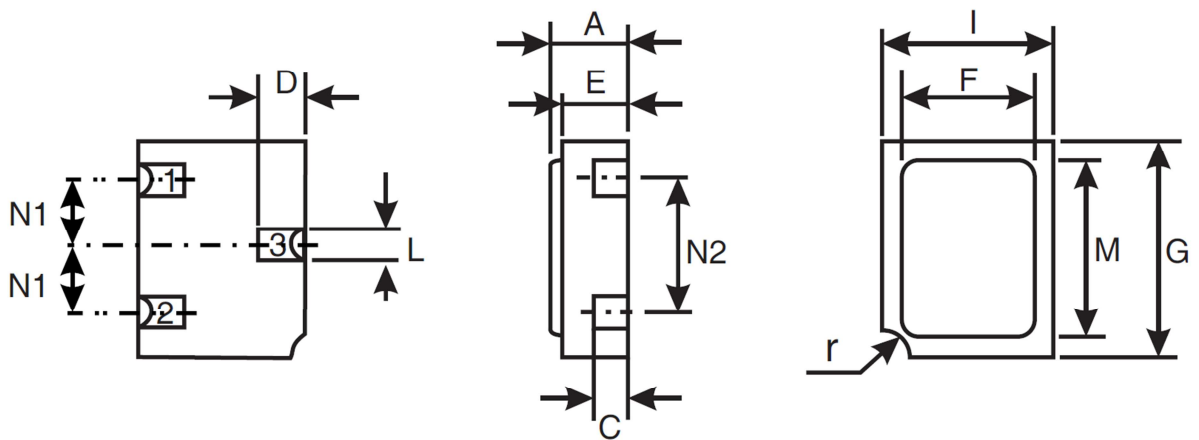


Symbols	Dimensions mm		Notes
	Min	Max	
A	4.32	5.33	
$\varnothing b$	0.406	0.533	2, 3
$\varnothing b2$	0.406	0.483	2, 3
$\varnothing D$	5.31	5.84	
$\varnothing D1$	4.52	4.95	
e	2.54 BSC		4
e1	1.27 BSC		4
F	-	0.762	
j	0.914	1.17	
k	0.711	1.22	5
L	12.7	-	2
L1	-	1.27	3
L2	6.35	-	3
a	45° BSC		1, 4, 6

NOTES:

1. Terminal identification is specified by reference to the tab position where lead 1 = emitter, lead 2 = base, lead 3 = collector.
2. Applies to all leads.
3. $\varnothing b2$ applies between L1 and L2. $\varnothing b$ applies between L2 and 12.7mm from the seating plane. Diameter is uncontrolled within L1 and beyond 12.7mm from the seating plane.
4. Leads having maximum diameter 0.483mm measured in the gauging plane 1.37 (+0.025, -0) mm below the seating plane of the device shall be within 0.178mm of their true position relative to a maximum-width-tab.
5. Measured from the maximum diameter of the actual device.
6. Tab centreline.

1.6.2 Chip Carrier Package (CCP) - 3 terminal

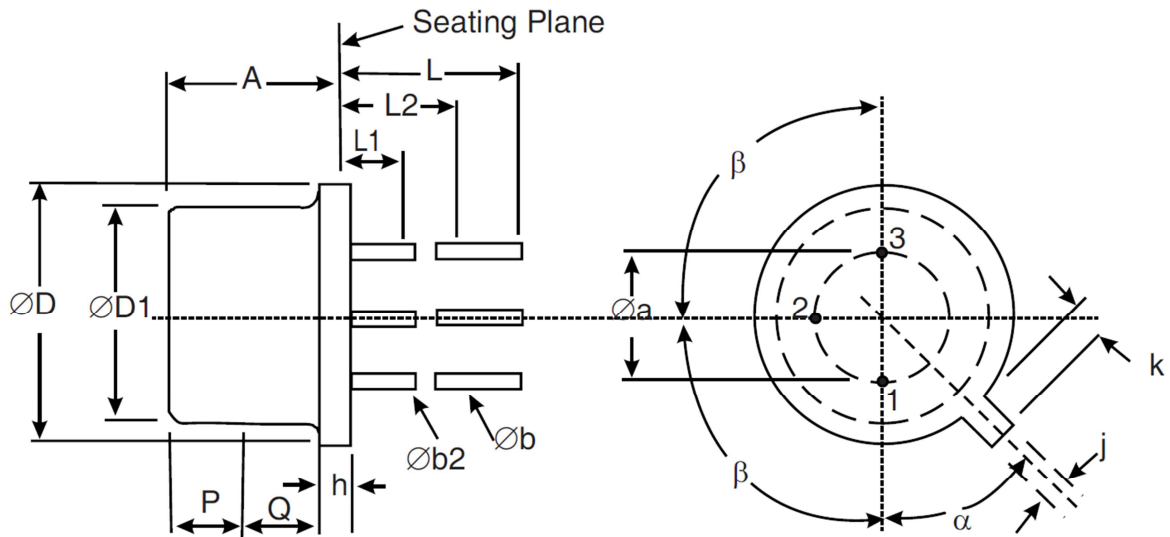


Symbols	Dimensions mm		Notes
	Min	Max	
A	1.15	1.5	
C	0.45	0.56	2
D	0.6	0.91	2
E	0.91	1.12	
F	1.9	2.15	
G	2.9	3.25	
I	2.4	.85	
L	0.4	0.6	2
M	2.4	2.65	
N1	0.855	1.055	
N2	1.8	2	
r	0.3 TYPICAL		1

NOTES:

1. Terminal identification is specified by reference to the corner notch position where terminal 1 = emitter, terminal 2 = base, terminal 3 = collector.
2. Applies to all terminals.

1.6.3 Metal Can Package (TO-39) - 3 lead



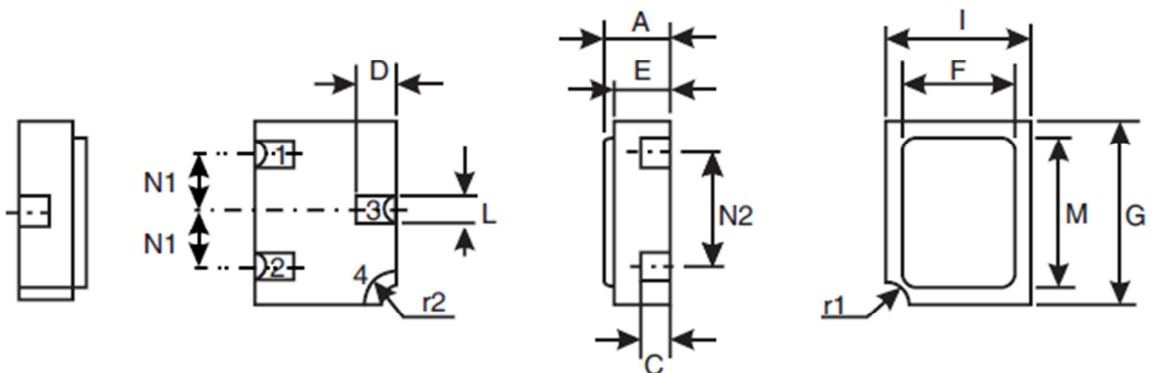
Symbols	Dimensions mm		Notes
	Min	Max	
$\varnothing a$	4.83	5.35	
A	6	6.6	
$\varnothing b$	0.4	0.533	2, 3
$\varnothing b2$	0.4	0.483	2, 3
$\varnothing D$	8.31	9.4	
$\varnothing D1$	7.75	8.51	
h	0.229	3.18	
j	0.71	0.864	
k	0.737	1.14	4
L	12.7	19	2
L1	-	1.27	2, 3
L2	6.35	-	2, 3
P	2.54	-	5
Q	-	-	6

Symbols	Dimensions mm		Notes
	Min	Max	
α	45° BSC		1, 7
β	90° BSC		1

NOTES:

1. Terminal identification is specified by reference to the tab position where Lead 1 = emitter, Lead 2 = base and Lead 3 = collector.
2. Applies to all leads.
3. $\varnothing b2$ applies between L1 and L2. $\varnothing b$ applies between L1 and 12.7mm from the seating plane. Diameter is uncontrolled within L1 and beyond 12.7mm from the seating plane.
4. Measured from the maximum diameter of the actual device.
5. This zone is controlled for automatic handling. The variation in actual diameter within this zone shall not exceed 0.254mm.
6. The details of outline in this zone are optional.
7. Measured from the Tab Centreline.

1.6.4 Chip Carrier Package (CCP) - 4 terminal



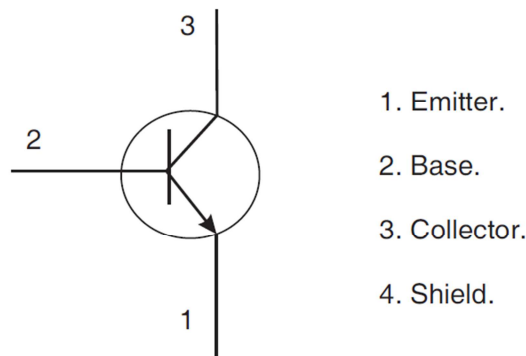
Symbols	Dimensions mm		Notes
	Min	Max	
A	1.15	1.5	
C	0.45	0.56	2
D	0.6	0.91	2
E	0.91	1.12	
F	1.9	2.15	
G	2.9	3.25	
I	2.4	2.85	
L	0.4	0.6	2
M	2.4	2.65	

Symbols	Dimensions mm		Notes
	Min	Max	
N1	0.855	1.055	
N2	1.8	2	
r1	0.3 TYPICAL		1
r2	0.56 TYPICAL		1

NOTES:

1. Terminal identification is specified by reference to the corner notch position where terminal 1 = emitter, terminal 2 = base, terminal 3 = collector, terminal 4 = shielding connected to the lid.
2. Applies to terminals 1, 2, 3.

1.7 FUNCTIONAL DIAGRAM



NOTES:

1. For TO-18 and TO-39, the collector is internally connected to the case.
2. For 3 terminal CCP (Variants 04, 05) the lid is not connected to any terminal.
3. For 4 terminal CCP (Variants 08, 09) the shielding terminal is connected to the lid.

1.8 MATERIALS AND FINISHES

Materials and finishes shall be as follows:

- (a) Case
For metal can packages, the case shall be hermetically sealed and have a metal body with hard glass seals.
For chip carrier packages, the case shall be hermetically sealed and have a ceramic body with a Kovar lid.
- (b) Leads/Terminals
As specified in Component Type Variants.

2 REQUIREMENTS

2.1 GENERAL

The complete requirements for procurement of the components specified herein are as stated in this specification and the ESCC Generic Specification. Permitted deviations from the Generic Specification, applicable to this specification only, are listed below.

Permitted deviations from the Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirement and do not affect the component's reliability, are listed in the appendices attached to this specification.

2.1.1 Deviations from the Generic Specification

- (a) Deviation from Screening Tests - Chart F3
High Temperature Reverse Bias Burn-in and the subsequent Final Measurements for HTRB shall be omitted.

2.2 MARKING

The marking shall be in accordance with the requirements of ESCC Basic Specification No. 21700 and as follows.

The information to be marked on the component shall be:

- (a) The ESCC qualified components symbol (for ESCC qualified components only).
- (b) The ESCC Component Number.
- (c) Traceability information.

2.3 TERMINAL STRENGTH

The test conditions for terminal strength, tested as specified in the ESCC Generic Specification, shall be as follows:

For TO-18 and TO-39, Test Condition: E, lead fatigue.

2.4 ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES
 Electrical measurements shall be performed at room, high and low temperatures.

2.4.1 Room Temperature Electrical Measurements
 The measurements shall be performed at $T_{amb} = +22 \pm 3^{\circ}C$.

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions	Limits		Units
				Min	Max	
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	3001	$I_C = 100\mu A$, Bias condition D	180	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	3011	$I_C = 1mA$, Bias condition D	160	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	3026	$I_E = 10\mu A$, Bias condition D	6	-	V
Collector-Base Cut-off Current	I_{CBO}	3036	$V_{CB} = 120V$, Bias condition D	-	50	nA
Emitter-Base Cut-off Current	I_{EBO}	3061	$V_{EB} = 4V$, Bias condition D	-	50	nA
Collector-Emitter Saturation Voltage	$V_{CE(sat)1}$	3071	$I_C = 10mA$ $I_B = 1mA$ Note 1	-	150	mV
	$V_{CE(sat)2}$		$I_C = 50mA$ $I_B = 5mA$ Note 1	-	200	mV
Base-Emitter Saturation Voltage	$V_{BE(sat)1}$	3066	$I_C = 10mA$ $I_B = 1mA$ Test condition A Note 1	-	1	V
	$V_{BE(sat)2}$		$I_C = 50mA$ $I_B = 5mA$ Test condition A Note 1	-	1	V

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions	Limits		Units
				Min	Max	
Forward-Current Transfer Ratio	h_{FE1}	3076	$V_{CE} = 5V ; I_C = 1mA$	80	-	-
	h_{FE2}		$V_{CE} = 5V ; I_C = 10mA$ Note 1	80	250	-
	h_{FE3}		$V_{CE} = 5V ; I_C = 50mA$ Note 1	30	-	-
Small-Signal Short-Circuit Forward-Current Transfer Ratio	h_{fe1}	3206	$V_{CE} = 10V,$ $I_{CE} = 1mA$ $f = 1kHz$ Note 2	50	200	-
High Frequency Small-Signal Short-Circuit Forward-Current Transfer Ratio	h_{fe2}	3306	$V_{CE} = 10V,$ $I_C = 10mA$ $f > 100MHz$ Note 2	1	-	-
Emitter-Base Capacitance	C_{ebo}	3240	$V_{EB} = 500mV,$ $I_C = 0A$ $f = 1MHz$ Note 2	-	20	pF
Output Capacitance	C_{obo}	3236	$V_{CB} = 10V$ $I_E = 0A$ $f = 1MHz$ Note 2	-	6	pF

NOTES:

1. Pulse measurement: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$
2. For AC characteristics read and record measurements shall be performed on a sample of 32 components with 0 failures allowed. Alternatively a 100% inspection may be performed.

2.4.2 High and Low Temperatures Electrical Measurements

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions Note 2	Limits		Units
				Min	Max	
Collector-Base Cut-off Current	I_{CBO}	3036	$T_{amb} = +150 (+0 -5)^{\circ}C$ $V_{CB} = 120V$, Bias condition D	-	50	μA
Forward-Current Transfer Ratio 2	h_{FE2}	3076	$T_{amb} = -55 (+5 -0)^{\circ}C$ $V_{CE} = 5V$ $I_C = 10mA$ Note 1	20	-	-

NOTES:

1. Pulse measurement: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
2. Read and record measurements shall be performed on a sample of 5 components with 0 failures allowed. Alternatively a 100% inspection may be performed.

2.5 PARAMETER DRIFT VALUES

Unless otherwise specified, the measurements shall be performed at $T_{amb} = +22 \pm 3^{\circ}C$.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The drift values (Δ) shall not be exceeded for each characteristic specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits			Units
		Drift Value Δ	Absolute		
			Min	Max	
Collector-Base Cut-off Current	I_{CBO}	± 5 or (1) $\pm 100\%$	-	50	nA
Collector-Emitter Saturation Voltage 2	$V_{CE(sat)2}$	± 30 or (1) $\pm 15\%$	-	200	mV
Forward-Current Transfer Ratio 2	h_{FE2}	$\pm 15\%$	80	250	-

NOTES:

1. Whichever is the greater referred to the initial value.

2.6 INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS

Unless otherwise specified, the measurements shall be performed at $T_{amb} = +22 \pm 3^{\circ}C$.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits		Units
		Min	Max	
Collector-Base Cut-off Current	I_{CBO}	-	50	nA
Collector-Emitter Saturation Voltage 2	$V_{CE(sat)2}$	-	200	mV
Forward-Current Transfer Ratio 2	h_{FE2}	80	250	-

2.7 POWER BURN-IN CONDITIONS

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T_{amb}	+25 to +50	$^{\circ}C$
Power Dissipation	P_{tot}	As per Maximum Ratings. Derate P_{tot1} at the chosen T_{amb} using the specified $R_{th(j-a)}$.	W
Collector-Base Voltage	V_{CB}	90	V

2.8 OPERATING LIFE CONDITIONS

The conditions shall be as specified for Power Burn-in.

2.9 TOTAL DOSE RADIATION TESTING

All lots shall be irradiated in accordance with ESCC Basic Specification No. 22900, low dose rate (window 2: 36 to 360 RAD/h).

2.9.1 Bias Conditions and Total Dose Level for Total dose Radiation Testing

The following bias conditions shall be used for Total Dose Radiation Testing:

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T_{amb}	$+20 \pm 5$	$^{\circ}C$
Bias Condition 1: Collector-Emitter Voltage	V_{CES}	$\geq 80\% V_{(BR)CEO}$	V
Bias Condition 2: Collector-Emitter Voltage	V_{CES}	0	V

The total dose level applied shall be as specified in the component type variant information herein or in the Purchase Order.

2.9.2 Electrical Measurements for Radiation Testing

Prior to irradiation testing the devices shall have successfully met Room Temperature Electrical Measurements specified herein.

Unless otherwise stated the measurements shall be performed at $T_{amb} = +22 \pm 3^{\circ}\text{C}$.

Unless otherwise specified the test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The parameters to be measured during and on completion of irradiation testing are shown below.

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions	Limits		Units
				Min	Max	
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	See Room Temperature Electrical Measurements	See Room Temperature Electrical Measurements	180	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	See Room Temperature Electrical Measurements	See Room Temperature Electrical Measurements	160	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	See Room Temperature Electrical Measurements	See Room Temperature Electrical Measurements	6	-	V
Collector-Base Cut-off Current	I_{CBO}	See Room Temperature Electrical Measurements	See Room Temperature Electrical Measurements	-	50	nA
Emitter-Base Cutoff Current	I_{EBO}	See Room Temperature Electrical Measurements	See Room Temperature Electrical Measurements	-	50	nA
Collector-Emitter Saturation Voltage	$V_{CE(sat)1}$	See Room Temperature Electrical Measurements	See Room Temperature Electrical Measurements	-	150	mV
	$V_{CE(sat)2}$			-	200	mV
Base-Emitter Saturation Voltage	$V_{BE(sat)1}$	See Room Temperature Electrical Measurements	See Room Temperature Electrical Measurements	-	1	V
	$V_{BE(sat)2}$			-	1	V

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions	Limits		Units
				Min	Max	
Forward-Current Transfer Ratio (post irradiation gain calculation) (Note 1)	[h _{FE1}]	3076	V _{CE} =5V, I _C = 1mA	[40]	-	-
	[h _{FE2}]		V _{CE} =5V, I _C = 10mA	[40]	250	-
	[h _{FE3}]		V _{CE} =5V, I _C = 50mA	[15]	-	-

NOTES:

1. The post-irradiation gain calculation of [h_{FE}], made using h_{FE} measurements from prior to and on completion of irradiation testing and after each annealing step if any, shall be as specified in MIL-STD-750 Method 1019.

APPENDIX 'A'
AGREED DEVIATIONS FOR STMICROELECTRONICS (F)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS																													
Deviations from Production Control-Chart F2	<p>Special In-Process Controls - Internal Visual Inspection. For CCP packages the criteria specified for voids in the fillet and minimum die mounting material around the visible die perimeter for die mounting defects may be omitted providing that a radiographic inspection to verify the die-attach process is performed on a sample basis in accordance with STMicroelectronics procedure 0076637.</p>																													
Deviations from Room Temperature Electrical Measurements	<p>All AC characteristics (Room Temperature Electrical Measurement Note 2) may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes AC characteristic measurements per the Detail Specification.</p> <p>A summary of the pilot lot testing shall be provided if required by the Purchase Order.</p> <p>Characteristics h_{fe2}, and C_{ebo}, shall be as follows:</p> <table border="1" data-bbox="549 1025 1455 1464"> <thead> <tr> <th rowspan="2">Characteristics</th> <th rowspan="2">Symbols</th> <th rowspan="2">MIL-STD-750 Test Method</th> <th rowspan="2">Test Conditions</th> <th colspan="2">Limits</th> <th rowspan="2">Units</th> </tr> <tr> <th>Min.</th> <th>Max.</th> </tr> </thead> <tbody> <tr> <td>High Frequency Small-Signal Short-Circuit Forward-Current Transfer Ratio</td> <td>h_{fe2}</td> <td>3306</td> <td>$V_{CE} = 10V$ $I_C = 10mA$ $f = 20MHz$ Note 2</td> <td>2.5</td> <td>-</td> <td>-</td> </tr> <tr> <td>Emitter-Base Capacitance</td> <td>C_{ebo}</td> <td>3240</td> <td>$V_{EB} = 500mV$ $I_C = 0A$ $f = 1MHz$ Note 2</td> <td>-</td> <td>45</td> <td>pF</td> </tr> </tbody> </table>							Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions	Limits		Units	Min.	Max.	High Frequency Small-Signal Short-Circuit Forward-Current Transfer Ratio	h_{fe2}	3306	$V_{CE} = 10V$ $I_C = 10mA$ $f = 20MHz$ Note 2	2.5	-	-	Emitter-Base Capacitance	C_{ebo}	3240	$V_{EB} = 500mV$ $I_C = 0A$ $f = 1MHz$ Note 2	-	45	pF
Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions	Limits		Units																								
				Min.	Max.																									
High Frequency Small-Signal Short-Circuit Forward-Current Transfer Ratio	h_{fe2}	3306	$V_{CE} = 10V$ $I_C = 10mA$ $f = 20MHz$ Note 2	2.5	-	-																								
Emitter-Base Capacitance	C_{ebo}	3240	$V_{EB} = 500mV$ $I_C = 0A$ $f = 1MHz$ Note 2	-	45	pF																								
Deviations from High and Low Temperatures Electrical Measurements	<p>All characteristics specified may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes characteristic measurements at high and low temperatures per the Detail Specification. A summary of the pilot lot testing shall be provided if required by the Purchase Order.</p>																													
Deviations from Screening Tests - Chart F3	<p>Solderability is not applicable unless specifically stipulated in the Purchase Order.</p>																													